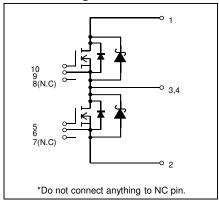
Application

- · Motor drive
- · Inverter, Converter
- · Photovoltaics, wind power generation.
- · Induction heating equipment.

Features

- 1) Low surge, low switching loss.
- 2) High-speed switching possible.
- 3) Reduced temperature dependence.

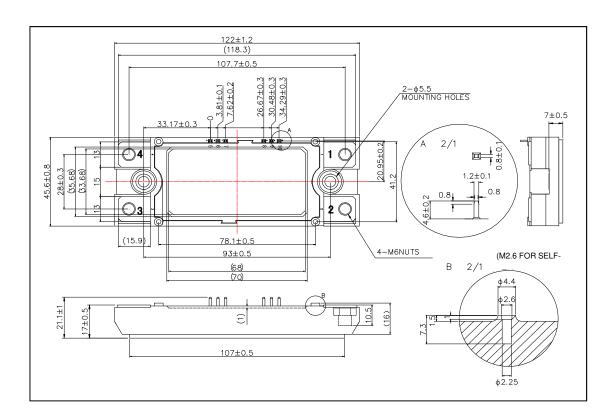
●Circuit diagram



Construction

This product is a half bridge module consisting of SiC-DMOS and SiC-SBD from ROHM.

● Dimensions & Pin layout (Unit : mm)

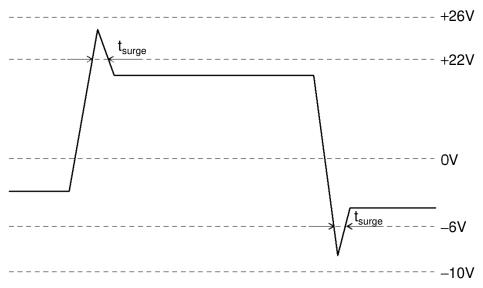


● Absolute maximum ratings (Tj = 25°C)

Parameter	Symbol	Conditions	Limit	Unit
Drain-source voltage	V_{DSS}	G-S short	1200	V
Gate-source voltage(+)	V	D-S short	22	V
Gate-source voltage(-)	$ V_{GSS}$	D-3 \$1101t	-6	V
G - S voltage (t _{surge} <300ns)	$V_{GSSsurge}$	D-S short	-10 to 26	V
Drain current *1	I _D	DC(Tc=60°C)	134	Α
	I _{DRM}	Pulse (Tc=60°C) 1ms *2	240	Α
Source current *1	I _S	DC(Tc =60°C) V _{GS} =18V	134	Α
	I _{SRM}	Pulse (Tc=60°C) 1ms V _{GS} =18V *2	240	Α
Total power disspation *3	Ptot	Tc=25°C	935	W
Max Junction Temperature	Tjmax		175	°C
Junction temperature	Tj		-40 to150	°C
Storage temperature	Tstg		-40 to125	°C
Isolation voltage	Visol	Terminals to baseplate, f=60Hz AC 1min.	2500	Vrms
Mounting torque		Main Terminals : M6 screw	4.5	N·m
	_	Mounting to heat shink: M5 screw	3.5	N·m

^(*1) Case temperature (Tc) is defined on the surface of base plate just under the chips.

Example of acceptable $V_{\mbox{\scriptsize GS}}$ waveform



^(*2) Repetition rate should be kept within the range where temperature rise if die should not exceed T_{jmax}.

^(*3) T_i is less than 175°C

●Electrical characteristics (Tj=25°C)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
On-state static Drain-Source Voltage	V _{DS(on)}	I _D =120A, V _{GS} =18V	T _j =25°C	_	2.1	3.2	V
			T _j =125°C	_	3.1	4.6	
			T _j =150°C		3.4	5.2	
Drain Cutoff Current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V		_	_	2	mA
Souce-Drain Voltage	V_{SD}	V _{GS} =0V, I _S =120A	T _j =25°C	1	1.7	2.1	V
			T _j =125°C	-	2.2	2.7	
			T _j =150°C	-	2.4	3.2	
	V SD	V _{GS} =18V, I _S =120A	T _j =25°C	-	1.3	_	
			T _j =125°C	-	1.7	_	
			T _j =150°C	-	1.8	_	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=10V$, $I_{D}=22mA$	1.6	2.3	4	V	
Gate-Source Leak Current	I _{GSS}	V_{GS} =22V, V_{DS} =0V		_	_	0.5	μА
		$V_{GS} = -6V, V_{DS} = 0V$		-0.5	_	_	
Switching Characteristics	$t_{d(on)}$	$\begin{array}{l} V_{GS(on)}{=}18V,\ V_{GS(off)}{=}0V\\ V_{DS}{=}600V\\ I_{D}{=}120A\\ R_{G}{=}3.9\Omega\\ \text{inductive load} \end{array}$		_	45	_	ns
	t _r			_	50	_	
	t _{rr}			-	30	_	
	$t_{d(off)}$			ı	170	_	
	t _f			-	60	_	
Input Capacitance	Ciss	$V_{DS}=10V$, $V_{GS}=0V$, $f=1MHz$		ı	14	_	nF
Gate Registance	R_{Gint}	T _j =25°C			1.8	_	Ω
Stray Inductance	Ls				25	_	nH
Creepage Distance	_	Terminal to heat sink			11.5	_	mm
		Terminal to terminal			19.0	_	mm
Clearance Distance	-	Terminal to heat sink			9.5	_	mm
		Terminal to terminal			13.0	_	mm
Junction-to-Case Thermal	R _{th} (j-c)	DMOSFET (1/2 module) *4		1	_	0.16	°C/W
Resistance	i ith() o)	SBD (1/2 module) *4		-	_	0.21	
Case-to-heat sink	R _{th} (c-f)	Case to heat sink, per 1 module, Thermal grease applied *5		-	0.035	_	
Thermal resistance	i ith(C-1)						

- (*4) Measurement of Tc is to be done at the point just under the chip.
- (*5) Typical value is measured by using thermally conductive grease of λ=0.9W/(m K).
- (*6) SiC devices have lower short cuicuit withstand capability due to high current density. Please be advised to pay careful attention to short cuicuit accident and try to adjust protection time to shutdown them as short as possible.
- (*7) If the Product is used beyond absolute maximum ratings defined in the Specifications, as its internal structure may be dameged, please replace such Product with a new one.

<Wavelength for Switching Test>

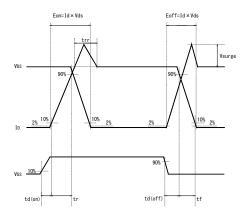
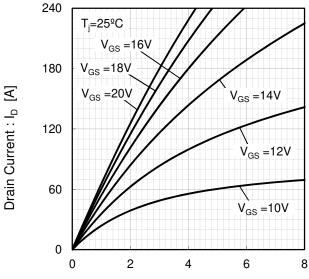
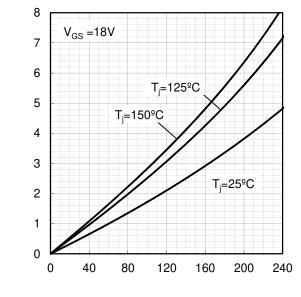


Fig.1 Typical Output Characteristics



Drain-Source Voltage : V_{DS} [V]

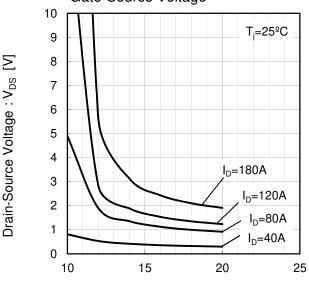
Fig.2 Drain-Source Voltage vs. Drain Current



Drain-Source Voltage: V_{DS} [V]

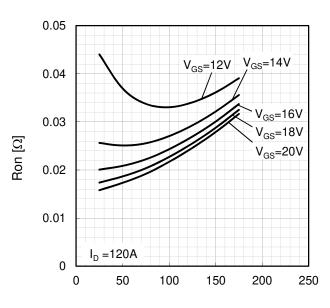
Drain Current : I_D [A]

Fig.3 Drain-Source Voltage vs. Gate-Source Voltage



Gate-Source Voltage : V_{GS} [V]

Fig.4 Ron vs Junction Temperature



Junction Temperature : T_i [ºC]

Fig.5 Forward characteristic of Diode

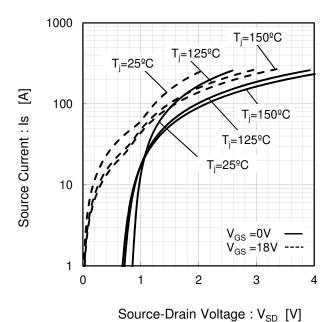
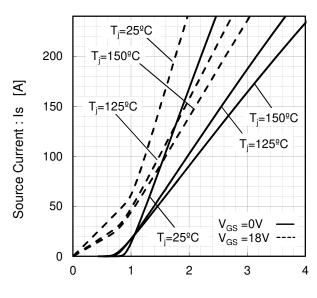


Fig.6 Forward characteristic of Diode



Source-Drain Voltage: V_{SD} [V]

Fig.7 Drain Current vs. Gate-Source Voltage

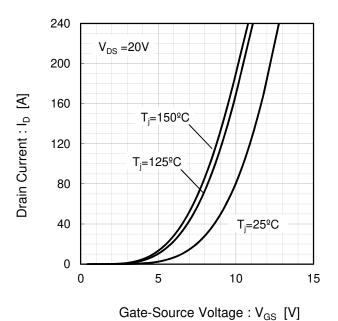
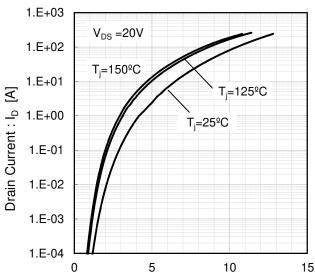


Fig.8 Drain Current vs. Gate-Source Voltage



Gate-Source Voltage : V_{GS} [V]

Fig.9 Switching Characteristics [T_i=25°C]

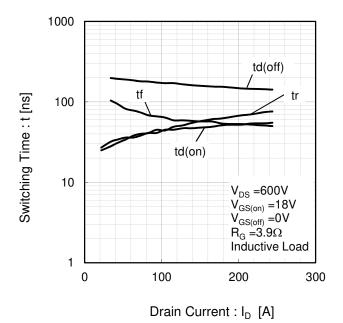


Fig.10 Switching Characteristics [T_i=125°C]

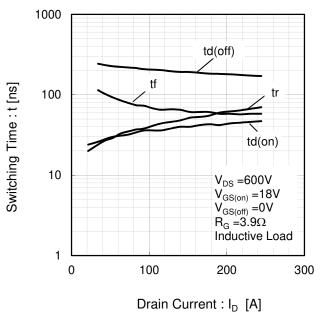


Fig.11 Switching Loss vs. Drain Current [$T_i=25^{\circ}C$]

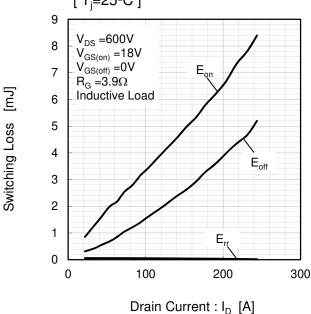
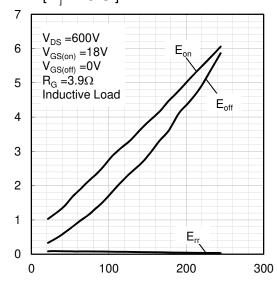
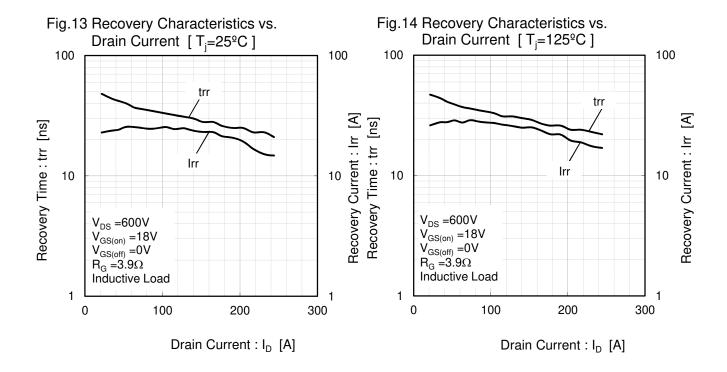
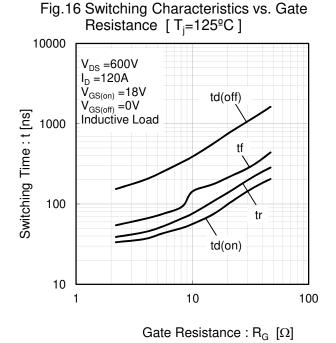


Fig.12 Switching Loss vs. Drain Current [$T_i=125^{\circ}C$]



Switching Loss [mJ]





ROHM

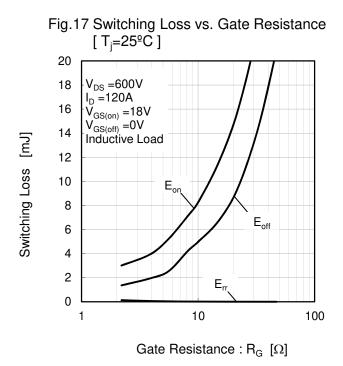


Fig.18 Switching Loss vs. Gate Resistance $[T_i=125^{\circ}C]$ 20 $V_{DS} = 600V$ $I_{D} = 120A$ 18 $V_{GS(off)} = 18V$ $V_{GS(off)} = 0V$ Inductive Load 16 14 12 10 E $\mathsf{E}_{\mathsf{off}}$ 8 6 4 2 0 10 100 Gate Resistance : $R_G [\Omega]$

Switching Loss [mJ]

Fig.19 Typical Capacitance vs. Drain-Source Voltage 1.E-07 $\mathsf{C}_{\mathsf{iss}}$ 1.E-08 Capasitance: C [nF] C_{oss} 1.E-09 $\boldsymbol{C}_{\text{rss}}$ 1.E-10 T_i=25ºC $V'_{GS} = 0V$ 1MHz 1.E-11 1 0.01 100

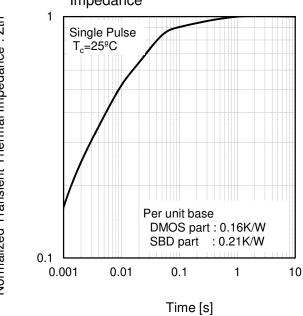
Drain-Source Voltage : V_{DS} [V]

Fig.20 Gate Charge Characteristics $[T_i=25^{\circ}C]$ 25 I_D =120A T_i=25°C $V_{DS} = 600V$ 20 15 10 5 0 0 200 400 600 800

Total Gate charge : Qg [nC]

Gate-Source Voltage: VGS [V]

Fig.21 Normalized Transient Thermal Impedance



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